

**N-Channel MOSFET** 

#### **General Description**

The WSD4080DN56 is the highest performance trench N-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD4080DN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

#### **Product Summery**

BVDSS	RDSON	ID
40V	4.5mΩ	85A

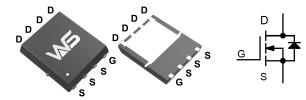
#### Applications

- Battery protection
- Load switch
- Uninterruptible power supply

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

### DFN5X6-8 Pin Configuration



#### Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units	
Vds	Drain-Source Voltage	40	V	
Vgs	Gate-Source Voltage	±20	V	
I₀@Tc=25°C	Continuous Drain Current, VGs @ 10V1	85	A	
I₀@Tc=100°C	Continuous Drain Current, VGs @ 10V1	58	A	
Ідм	Pulsed Drain Current <sub>2</sub>	100	A	
EAS	Single Pulse Avalanche Energy <sub>3</sub>	110.5	mJ	
las	Avalanche Current	47	A	
Pp@Tc=25°C	Total Power Dissipation <sub>4</sub>	52.1	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Reja	Thermal Resistance Junction-Ambient 1	62	°C/W	
Rejc	Thermal Resistance Junction-Case1	2.4	°C/W	



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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , I⊵=250uA	40			V
Rds(on)	Static Drain-Source On-Resistance2	Vgs=10V , Id=10A		4.5	6.5	mΩ
		Vgs=4.5V , Ib=5A		6.4	8.5	
VGS(th)	Gate Threshold Voltage	Vgs=Vds , Id =250uA	1.0		2.5	V
lpss	Drain-Source Leakage Current	Vds=32V , Vgs=0V , Tj=25°C			1	uA
1055		Vds=32V , Vgs=0V , Tj=55°C			5	
lgss	Gate-Source Leakage Current	Vgs=±20V , Vds=0V			±100	nA
gfs	Forward Transconductance	Vds=10V , Id=5A		27		S
Qg	Total Gate Charge (4.5V)	Vds=20V , Vgs=4.5V , Id=10A		20		nC
Qgs	Gate-Source Charge			5.8		
Qgd	Gate-Drain Charge			9.5		
Td(on)	Turn-On Delay Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A		15.2		- ns
Tr	Rise Time			8.8		
Td(off)	Turn-Off Delay Time			74		
Tf	Fall Time			7		
Ciss	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		2354		pF
Coss	Output Capacitance			215		
Crss	Reverse Transfer Capacitance			175		
ls	Continuous Source Current1,5	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			70	А
Vsd	Diode Forward Voltage2	Vgs=0V , Is=1A , TJ=25°C			1	V

Note :

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width  $\leqq$  300us , duty cycle  $\leqq$  2%

3. The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=47A

4.The power dissipation is limited by 150  $^\circ\!\mathrm{C}$  junction temperature

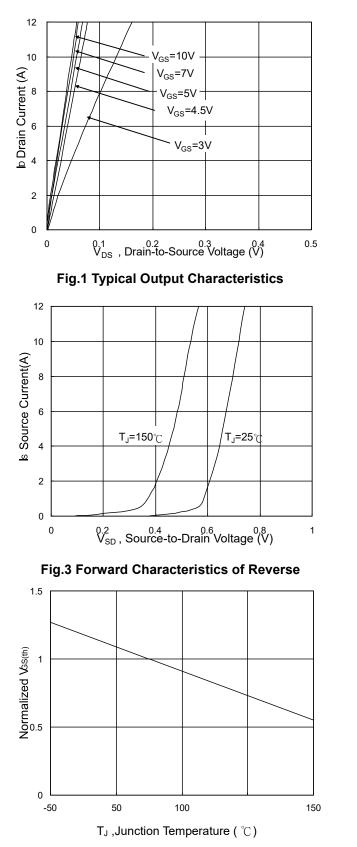
5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

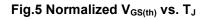


# WSD4080DN56

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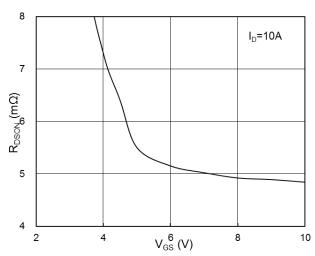


Fig.2 On-Resistance vs. G-S Voltage

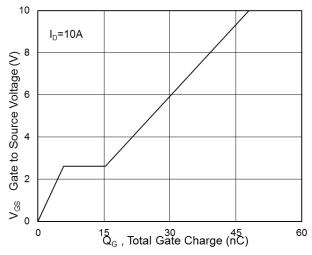


Fig.4 Gate-Charge Characteristics

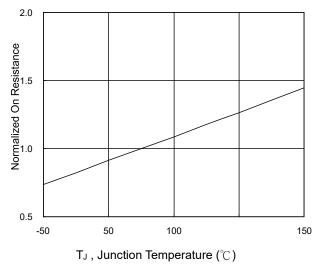


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





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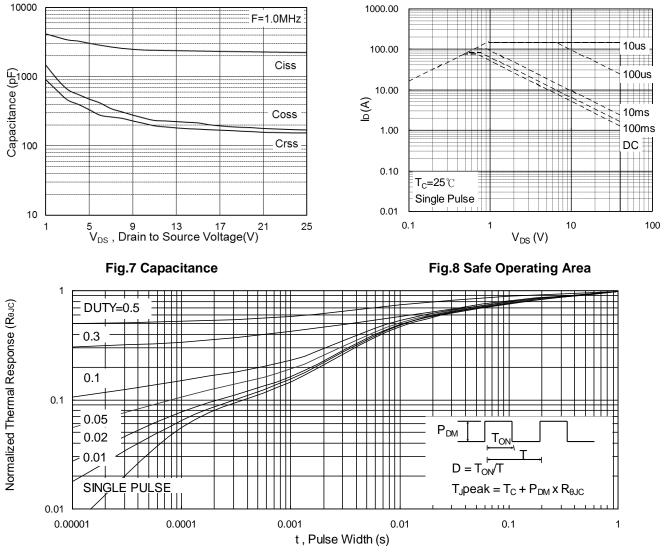
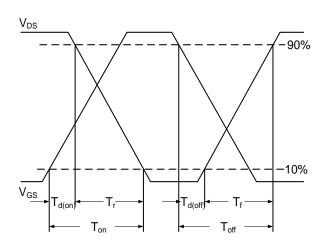


Fig.9 Normalized Maximum Transient Thermal Impedance





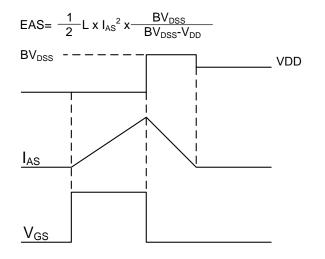


Fig.11 Unclamped Inductive Switching Wave



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